

LISTING OF CLAIMS

1. (Original) A method of fabricating a memory cell, comprising:
 - forming a first conductive layer over a substrate;
 - forming a superionic conductor over said first conductive layer;
 - forming a polymer layer over said superionic conductor in a manner which produces a layer of mobile ions between said polymer layer and said superionic conductor; and
 - forming a second conductive layer over said polymer layer.
2. (Original) The method of claim 1, wherein said superionic conductor is formed from a transition metal complex.
3. (Original) The method of claim 1, wherein said superionic conductor is selected from a group consisting of CuBr and Cu₂Se.
4. (Original) The method of claim 1, wherein said polymer layer is formed from vinyl monomers.
TP 5. (Original) The method of claim 5, wherein said vinyl monomers are selected from a group consisting of methacrylates, acrylates, styrenes, vinylpyridines, acrylonitrile, and acrylamides.
6. (Original) The method of claim 1, wherein forming the polymer layer comprises placing monomers in contact with said superionic conductive layer such that said superionic conductor acts as an initiator to form polymers from said monomers.